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(54) FBAR STRURCTURE AND MANUFACTURING METHOD OF SAME

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(57)**ABSTRACT**

A method for forming a film bulk acoustic resonator (FBAR) structure includes: sequentially forming a top electrode layer, a piezoelectric layer, and a bottom electrode layer on a first substrate; patterning the bottom electrode layer to form a bottom electrode; forming a dielectric layer on the bottom electrode; bonding a bonding substrate onto the dielectric layer; removing the first substrate; patterning the top electrode layer to form a top electrode; forming an opening in the bonding substrate; selectively removing a portion of the dielectric layer to form a cavity; and bonding a bottom cap wafer onto the bonding substrate to seal the

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